



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

**SOD-123 封装二极管/SOD-123 Plastic-Encapsulate Diodes**

## BAT42W&BAT43W (SCHOTTKY DIODE)

### 特点/Features :

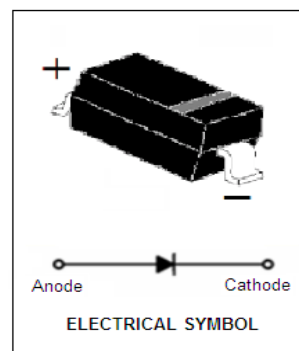
- 正向导通电压低 ;
- 极小的导通与恢复时间 ;
- 适合表面安装 ;

### 用途/Applications :

高速开关电路。

印章/ Marking: BAT42W: S7

BAT43W: S8



### 极限参数/Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Value	Unit
Peak Repetitive Peak Reverse Voltage	$V_{RRM}$	30	V
Working Peak	$V_{RWM}$		
DC Blocking Voltage	$V_R$		
RMS Reverse Voltage	$V_{R(RMS)}$	21	V
Forward Continuous Current	$I_{FM}$	200	mA
Repetitive Peak Forward Current (@t≤1S)	$I_{FSM}$	500	mA
Power Dissipation	$P_d$	500	mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$	200	°C/mW
Junction Temperature	$T_j$	125	°C
Storage Temperature	$T_{stg}$	-55~150	°C

### 电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最小值	典型值	最大值	单位
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=10 \mu A$	30			V
Forward Voltage	All Types	$I_F=200mA$			1.0	V
	BAT42W	$I_F=10mA$			0.4	V
	BAT42W	$I_F=50mA$			0.65	V
	BAT43W	$I_F=2mA$	0.26		0.33	V
	BAT43W	$I_F=15mA$			0.45	V
Reverse Current	$I_{RM}$	$V_R=25V$			0.5	$\mu A$
Capacitance Between Terminals	$C_T$	$V_R=0V, f=1.0MHz$			10	pF
Reverse Recovery Time	$t_{rr}$	$I_F=I_R=10mA,$ $I_{rr}=0.1 \times I_R, R_L=100 \Omega$			5	nS



### 典型特性曲线图/Typical Characteristics

